

CSD17484F4 30V N 沟道 FemtoFET™ MOSFET

1 特性

- 低导通电阻
- 超低 Q_g 和 Q_{gd}
- 低阈值电压
- 超小封装尺寸 (0402 外壳尺寸)
 - $1.0\text{mm} \times 0.6\text{mm}$
- 超薄型封装
 - 厚度为 0.2mm
- 集成型 ESD 保护二极管
 - 额定值 $> 4\text{kV}$ HBM
 - 额定值 $> 2\text{kV}$ CDM
- 无铅且无卤素
- 符合 RoHS

2 应用

- 针对负载开关应用进行了优化
- 针对通用开关应用进行了优化
- 电池应用
- 手持式和移动类应用

3 说明

该 $99\text{m}\Omega$ 、 30V N 沟道 FemtoFET™ MOSFET 经过设计和优化，能够最大限度地减小在许多手持式和移动应用中占用的空间。这项技术能够在替代标准小信号 MOSFET 的同时将封装尺寸减小至少 60%。

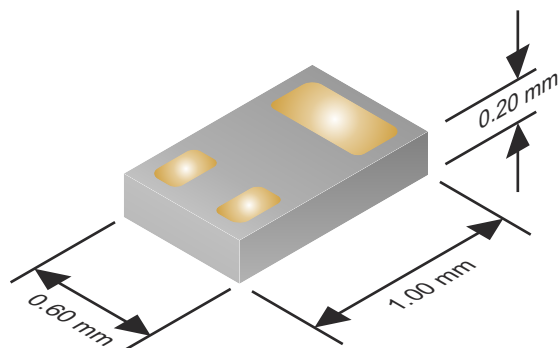


图 3-1. 典型器件尺寸

产品概要

$T_A = 25^\circ\text{C}$		典型值	单位
V_{DS}	漏源电压	30	V
Q_g	总栅极电荷 (4.5V)	920	pC
Q_{gd}	栅极电荷 (栅极到漏极)	75	pC
$R_{DS(on)}$	漏源导通电阻	$V_{GS} = 1.8\text{V}$	170
		$V_{GS} = 2.5\text{V}$	125
		$V_{GS} = 4.5\text{V}$	107
		$V_{GS} = 8.0\text{V}$	99
$V_{GS(th)}$	阈值电压	0.85	V

器件信息(1)

器件	数量	介质	封装	配送
CSD17484F4	3000	7 英寸卷带	Femto (0402)	卷带包装
CSD17484F4T	250		$1.00\text{mm} \times 0.60\text{mm}$ 基板栅格阵列 (LGA)	

- (1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

绝对最大额定值

$T_A = 25^\circ\text{C}$		值	单位
V_{DS}	漏源电压	30	V
V_{GS}	栅源电压	12	V
I_D	持续漏极电流 ⁽¹⁾	3.0	A
I_{DM}	脉冲漏极电流 ⁽¹⁾⁽²⁾	18	A
I_G	持续栅极钳位电流	35	mA
	脉冲栅极钳位电流 ⁽²⁾	350	
P_D	功率耗散	500	mW
$V_{(ESD)}$	人体放电模型 (HBM)	4	kV
	充电器件模型 (CDM)	2	
T_J 、 T_{stg}	工作结温， 贮存温度	-55 至 150	$^\circ\text{C}$
E_{AS}	雪崩能量，单脉冲 $I_D = 7.1\text{A}$ ， $L = 0.1\text{mH}$ ， $R_G = 25\Omega$	2.5	mJ

- (1) 典型 $R_{\theta JA} = 85^\circ\text{C/W}$ (在 0.06 英寸 (1.52mm) 厚的 FR4 PCB 上安装 1 平方英寸 (6.45cm²)、2oz、0.071mm 厚的铜焊盘时)。
- (2) 脉冲持续时间 $\leq 100\mu\text{s}$ ，占空比 $\leq 1\%$ 。

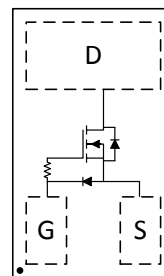


图 3-2. 顶视图



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4 Revision History

Changes from Revision C (December 2019) to Revision D (February 2022)	Page
• Added FemtoFET Surface Mount Guide note.....	9
Changes from Revision B (September 2017) to Revision C (December 2019)	Page
• Changed On-State Resistance vs Gate-to-Source Voltage by truncating V_{GS} from 20 V to 12 V.....	4
Changes from Revision A (August 2017) to Revision B (September 2017)	Page
• Deleted the <i>CSD68830F4 Embossed Carrier Tape Dimensions</i> section.....	9
Changes from Revision * (May 2015) to Revision A (August 2017)	Page
• Added the § 6.1 and the § 6 sections	7
• Updated the § 7 section.....	8

5 Specifications

5.1 Electrical Characteristics

$T_A = 25^\circ\text{C}$ (unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV _{DSS}	Drain-to-source voltage	V _{GS} = 0 V, I _{DS} = 250 μA	30			V
I _{DSS}	Drain-to-source leakage current	V _{GS} = 0 V, V _{DS} = 24 V			100	nA
I _{GSS}	Gate-to-source leakage current	V _{DS} = 0 V, V _{GS} = 12 V			50	nA
V _{GS(th)}	Gate-to-source threshold voltage	V _{DS} = V _{GS} , I _{DS} = 250 μA	0.65	0.85	1.10	V
R _{DS(on)}	Drain-to-source on-resistance	V _{GS} = 1.8 V, I _{DS} = 0.5 A		170	270	mΩ
		V _{GS} = 2.5 V, I _{DS} = 0.5 A		125	160	
		V _{GS} = 4.5 V, I _{DS} = 0.5 A		107	128	
		V _{GS} = 8 V, I _{DS} = 0.5 A		99	121	
g _{fs}	Transconductance	V _{DS} = 15 V, I _{DS} = 0.5 A		4		S
DYNAMIC CHARACTERISTICS						
C _{iss}	Input capacitance	V _{GS} = 0 V, V _{DS} = 15 V, f = 1 MHz		150	195	pF
C _{oss}	Output capacitance			44	57	pF
C _{rss}	Reverse transfer capacitance			2.2	2.9	pF
R _G	Series gate resistance			8		Ω
Q _g	Gate charge total (4.5 V)	V _{DS} = 15 V, I _{DS} = 0.5 A		920	1200	pC
Q _g	Gate charge total (8.0 V)			1570	2040	pC
Q _{gd}	Gate charge gate-to-drain			75		pC
Q _{gs}	Gate charge gate-to-source			280		pC
Q _{g(th)}	Gate charge at V _{th}			140		pC
Q _{oss}	Output charge	V _{DS} = 15 V, V _{GS} = 0 V		1400		pC
t _{d(on)}	Turnon delay time	V _{DS} = 15 V, V _{GS} = 4.5 V, I _{DS} = 0.5 A, R _G = 2 Ω		3		ns
t _r	Rise time			1		ns
t _{d(off)}	Turnoff delay time			11		ns
t _f	Fall time			4		ns
DIODE CHARACTERISTICS						
V _{SD}	Diode forward voltage	I _{SD} = 0.5 A, V _{GS} = 0 V		0.73	0.9	V
Q _{rr}	Reverse recovery charge	V _{DS} = 15 V, I _F = 0.5 A, di/dt = 300 A/ μs		1300		pC
t _{rr}	Reverse recovery time			6.2		ns

5.2 Thermal Information

$T_A = 25^\circ\text{C}$ (unless otherwise stated)

THERMAL METRIC		TYPICAL VALUES	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance ⁽¹⁾	85	$^\circ\text{C}/\text{W}$
	Junction-to-ambient thermal resistance ⁽²⁾	245	

- (1) Device mounted on FR4 material with 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu.
 (2) Device mounted on FR4 material with minimum Cu mounting area.

5.3 Typical MOSFET Characteristics

$T_A = 25^\circ\text{C}$ (unless otherwise stated)

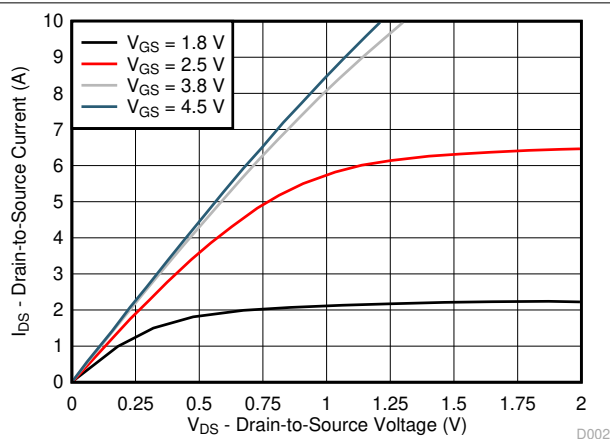


图 5-1. Saturation Characteristics

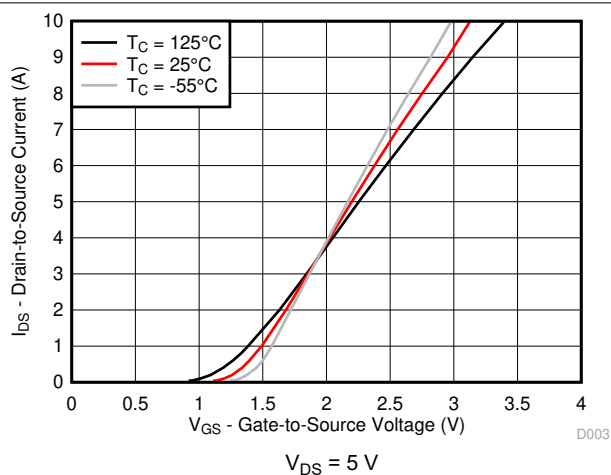


图 5-2. Transfer Characteristics

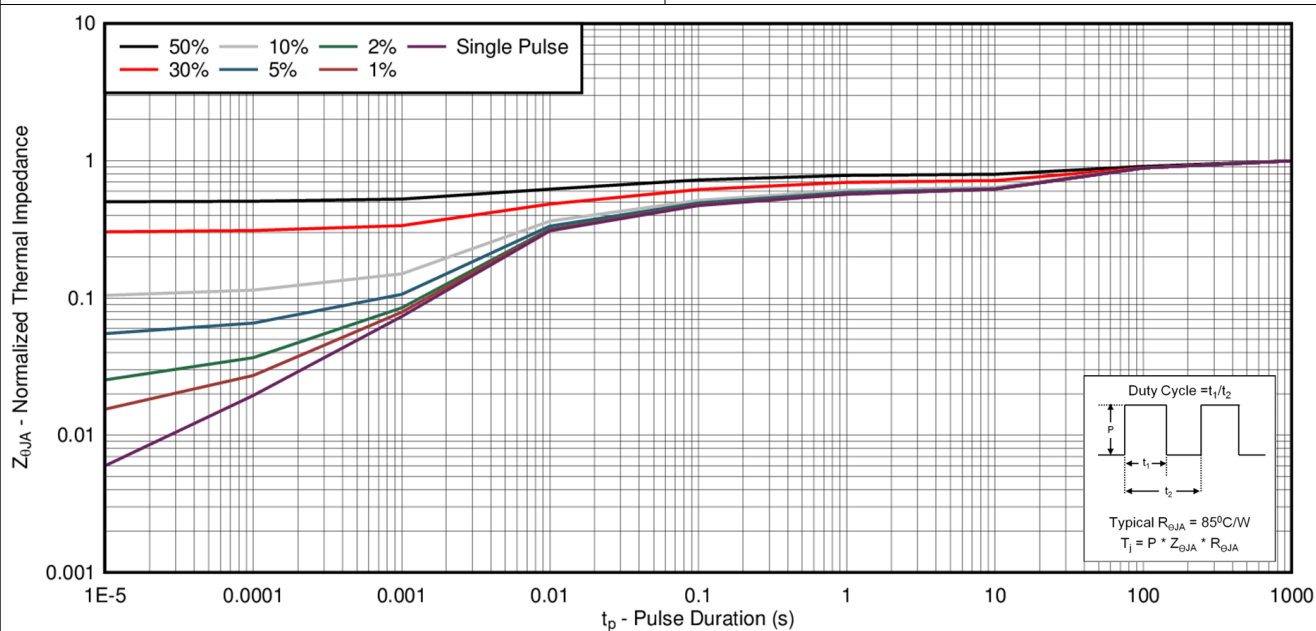


图 5-3. Transient Thermal Impedance

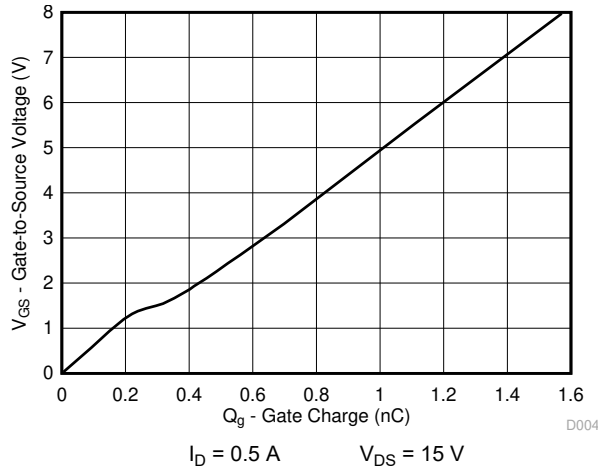


图 5-4. Gate Charge

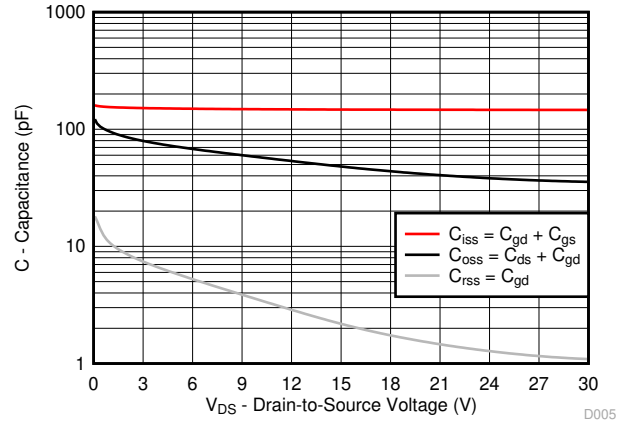


图 5-5. Capacitance

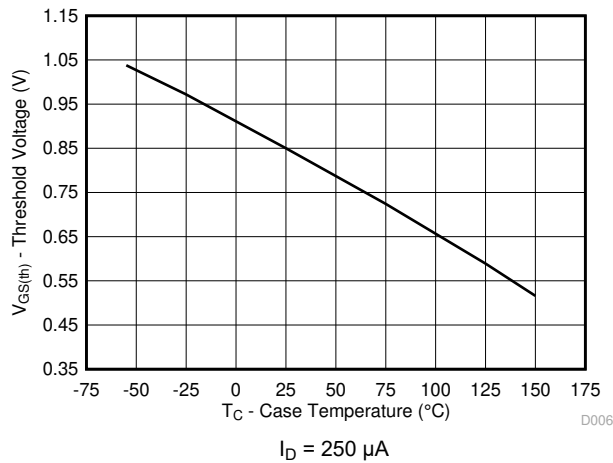


图 5-6. Threshold Voltage vs Temperature

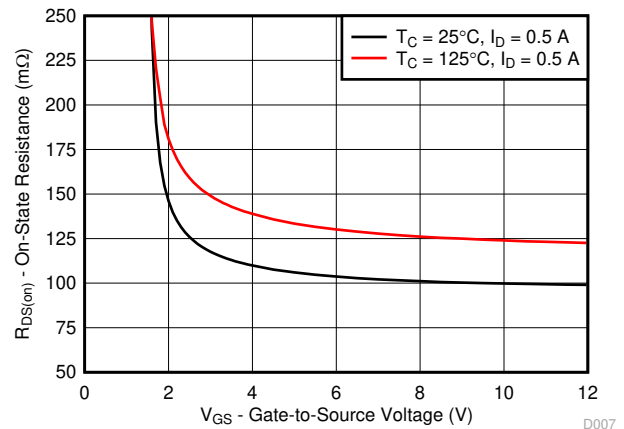


图 5-7. On-State Resistance vs Gate-to-Source Voltage

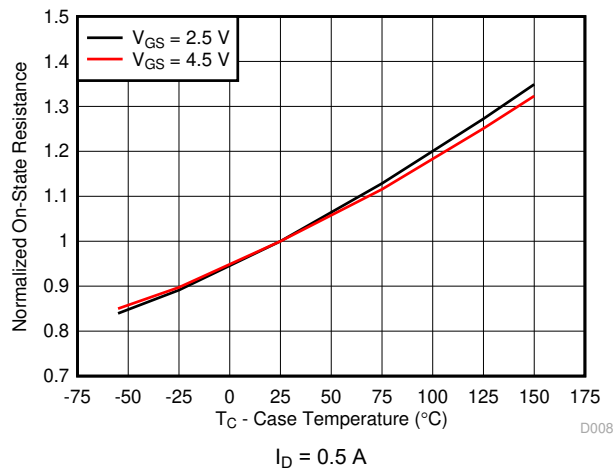


图 5-8. Normalized On-State Resistance vs Temperature

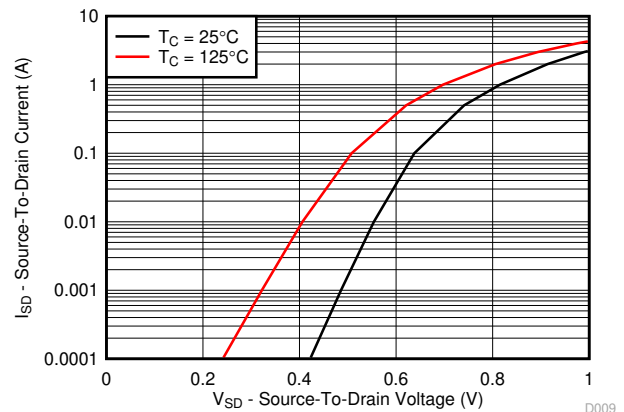


图 5-9. Typical Diode Forward Voltage

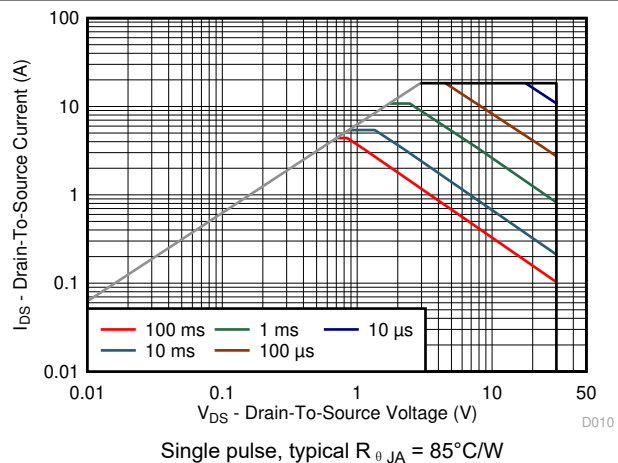


图 5-10. Maximum Safe Operating Area

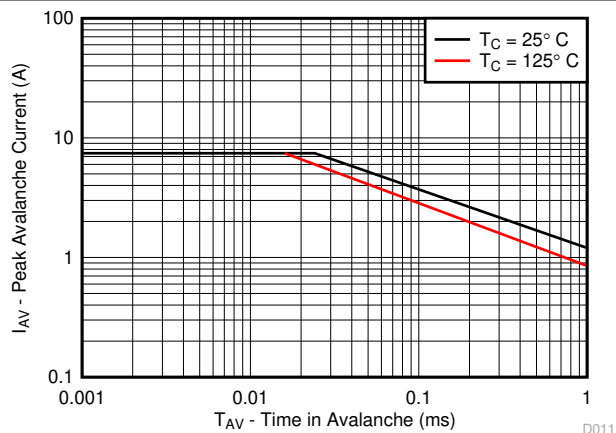


图 5-11. Single Pulse Unclamped Inductive Switching

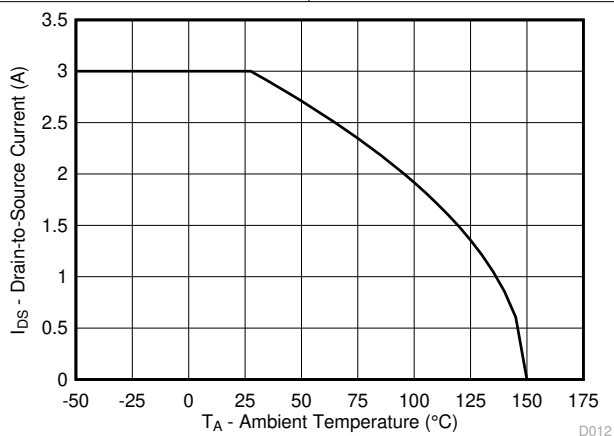


图 5-12. Maximum Drain Current vs Temperature

6 Device and Documentation Support

6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

6.2 Trademarks

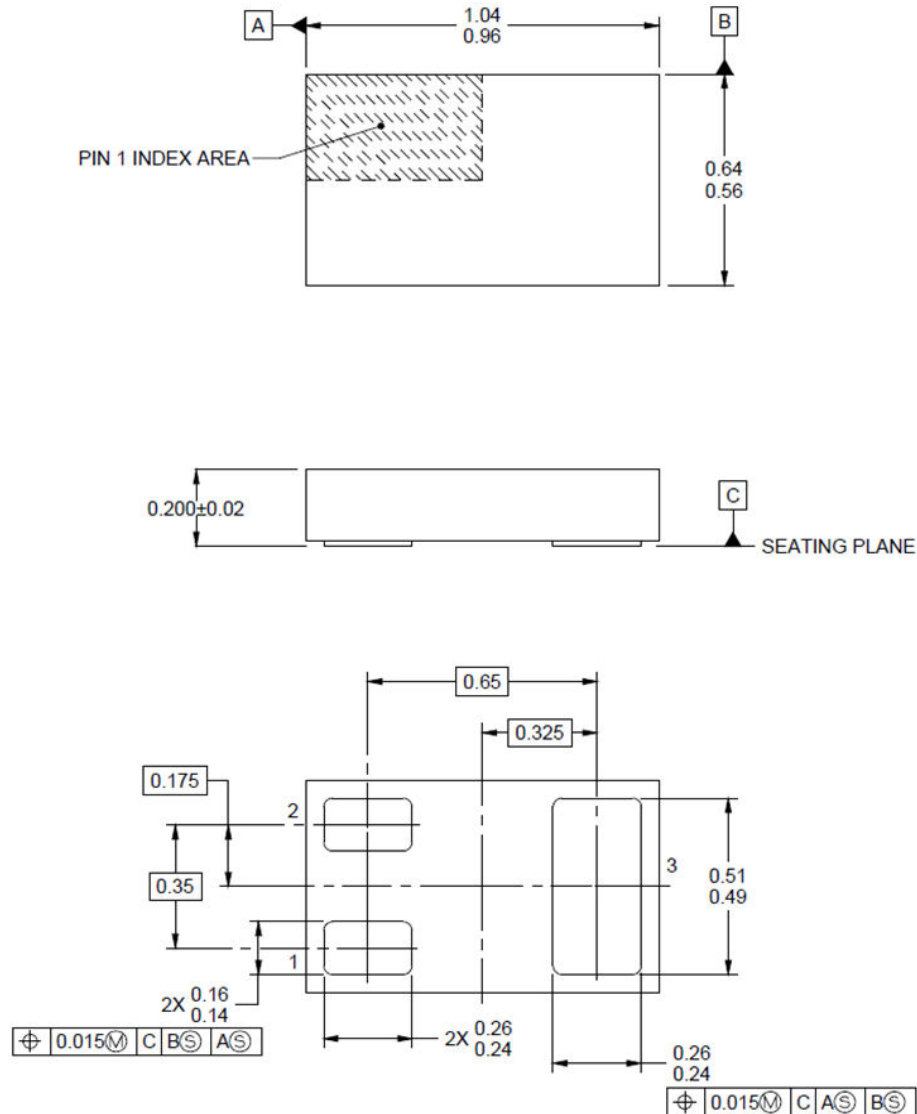
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7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Mechanical Dimensions

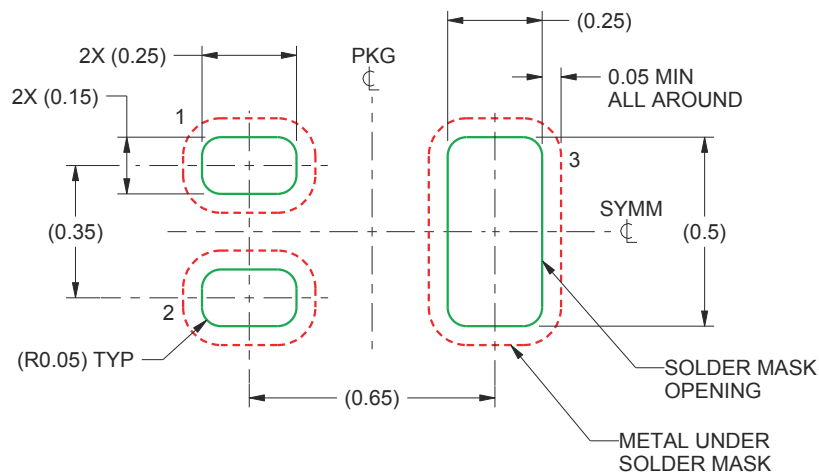


- A. All linear dimensions are in millimeters (dimensions and tolerancing per ASME Y14.5M-1994).
- B. This drawing is subject to change without notice.
- C. This package is a PB-free solder land design.

表 7-1. Pin Configuration

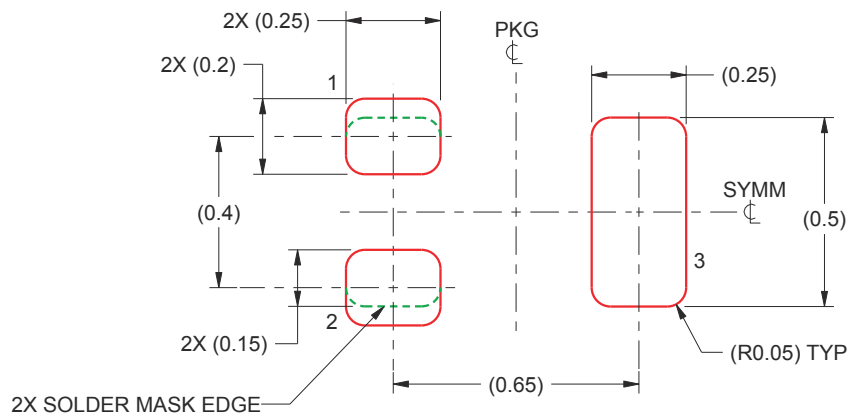
POSITION	DESIGNATION
Pin 1	Gate
Pin 2	Source
Pin 3	Drain

7.2 Recommended Minimum PCB Layout



- A. All dimensions are in millimeters.
- B. For more information, see [FemtoFET Surface Mount Guide](#) (SLRA003D).

7.3 Recommended Stencil Pattern



- A. All dimensions are in millimeters.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD17484F4	ACTIVE	PICOSTAR	YJJ	3	3000	RoHS & Green	NIAU	Level-1-260C-UNLIM	-55 to 150	G2	Samples
CSD17484F4T	ACTIVE	PICOSTAR	YJJ	3	250	RoHS & Green	NIAU	Level-1-260C-UNLIM	-55 to 150	G2	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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